

## COMPLEMENTARY SILICON POWER DARLINGTON TRANSISTORS

- SGS-THOMSON PREFERRED SALESTYPES
- COMPLEMENTARY PNP - NPN DEVICES
- INTEGRATED ANTIPARALLEL COLLECTOR-EMITTER DIODE

### APPLICATIONS

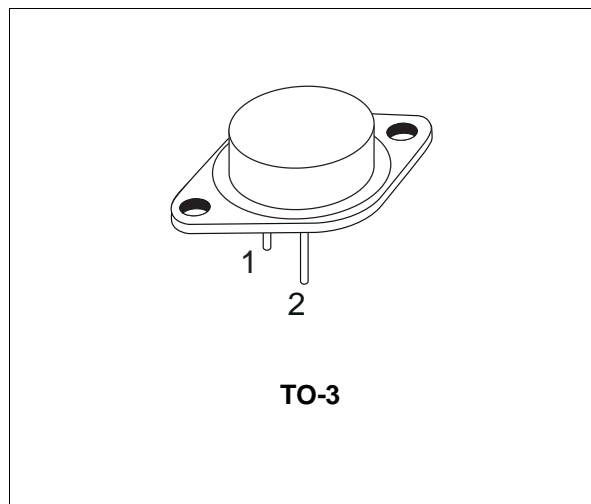
- LINEAR AND SWITCHING INDUSTRIAL EQUIPMENT

### DESCRIPTION

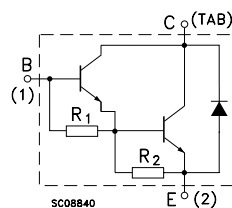
The 2N6284 is a silicon epitaxial-base NPN power transistor in monolithic Darlington configuration mounted in Jedec TO-3 metal case.

It is intended for general purpose amplifier and low frequency switching applications.

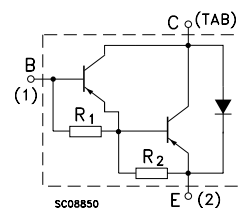
The complementary PNP types is 2N6287.



### INTERNAL SCHEMATIC DIAGRAM



R<sub>1</sub> Typ. = 8 KΩ



R<sub>2</sub> Typ. = 60 Ω

### ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value		Unit
		NPN	2N6284	
		PNP	2N6287	
V <sub>CB0</sub>	Collector-Base Voltage (I <sub>E</sub> = 0)		100	V
V <sub>CE0</sub>	Collector-Emitter Voltage (I <sub>B</sub> = 0)		100	V
V <sub>EBO</sub>	Emitter-Base Voltage (I <sub>C</sub> = 0)		5	V
I <sub>C</sub>	Collector Current		20	A
I <sub>CM</sub>	Collector Peak Current		40	A
I <sub>B</sub>	Base Current		0.5	A
P <sub>tot</sub>	Total Dissipation at T <sub>c</sub> ≤ 25 °C		160	W
T <sub>stg</sub>	Storage Temperature		-65 to 200	°C
T <sub>j</sub>	Max. Operating Junction Temperature		200	°C

For PNP types voltage and current values are negative.

**THERMAL DATA**

R <sub>thj-case</sub>	Thermal Resistance Junction-case	Max	1.09	°C/W
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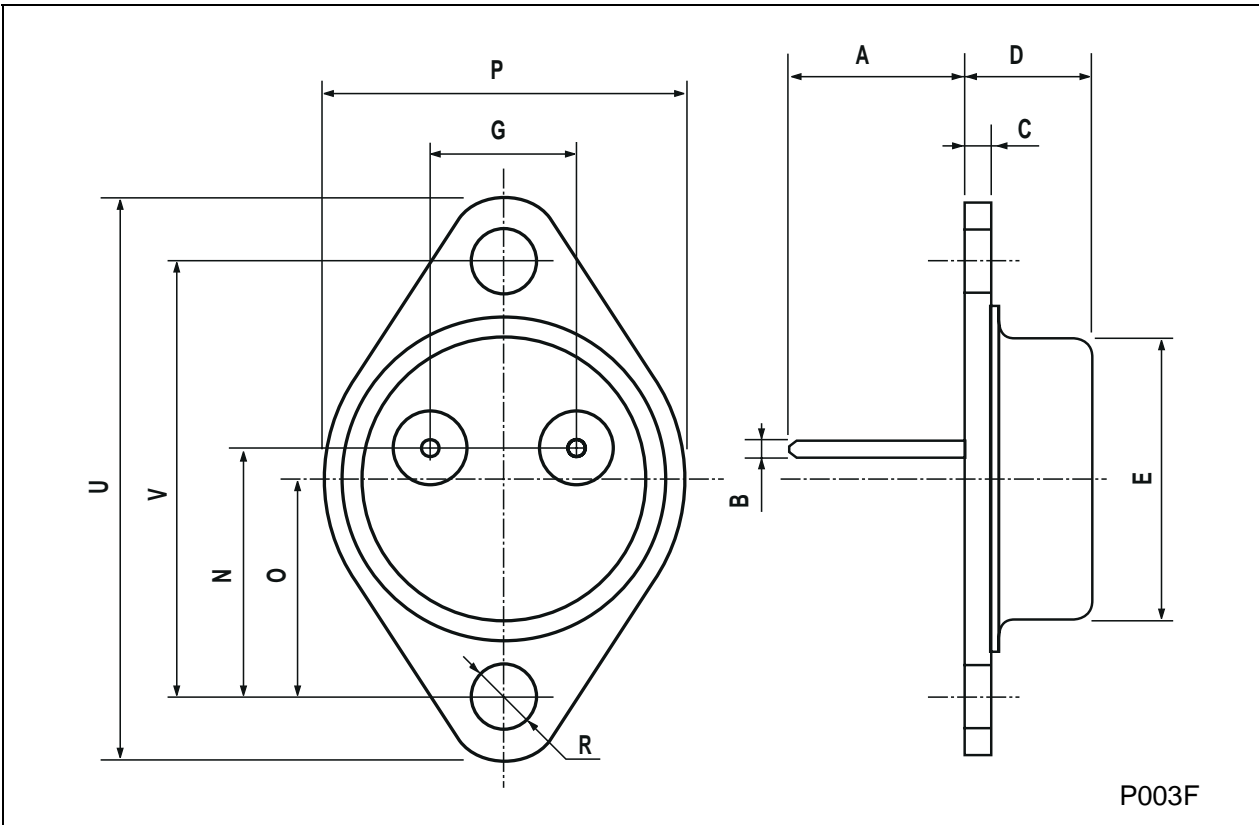
**ELECTRICAL CHARACTERISTICS** (T<sub>case</sub> = 25 °C unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I <sub>CEV</sub>	Collector Cut-off Current (V <sub>BE</sub> = -1.5V)	V <sub>CE</sub> = rated V <sub>CEO</sub> V <sub>CE</sub> = rated V <sub>CEO</sub> T <sub>C</sub> = 150 °C			0.5 5	mA mA
I <sub>CEO</sub>	Collector Cut-off Current (I <sub>B</sub> = 0)	V <sub>CE</sub> = 50 V			1	mA
I <sub>EBO</sub>	Emitter Cut-off Current (I <sub>C</sub> = 0)	V <sub>EB</sub> = 5 V			2	mA
V <sub>CEO(sus)*</sub>	Collector-Emitter Sustaining Voltage	I <sub>C</sub> = 100 mA	100			V
V <sub>CE(sat)*</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 10 A    I <sub>B</sub> = 40 mA I <sub>C</sub> = 20 A    I <sub>B</sub> = 200 mA			2 3	V V
V <sub>BE(sat)*</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 20 A    I <sub>B</sub> = 200 mA			4	V
V <sub>BE*</sub>	Base-Emitter Voltage	I <sub>C</sub> = 10 A    V <sub>CE</sub> = 3 V			2.8	V
h <sub>FE*</sub>	DC Current Gain	I <sub>C</sub> = 10 A    V <sub>CE</sub> = 3 V I <sub>C</sub> = 20 A    V <sub>CE</sub> = 3 V	750 100		18000	
h <sub>fe</sub>	Small Signal Current Gain	I <sub>C</sub> = 3 A    V <sub>CE</sub> = 10 V    f = 1KHz	300			
C <sub>CBO</sub>	Collector Base Capacitance	I <sub>E</sub> = 0    V <sub>CB</sub> = 10 V    f = 100KHz for <b>NPN types</b> for <b>PNP types</b>			400 600	pF pF

\* Pulsed: Pulse duration = 300 μs, duty cycle 1.5 %

**TO-3 MECHANICAL DATA**

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	11.00		13.10	0.433		0.516
B	0.97		1.15	0.038		0.045
C	1.50		1.65	0.059		0.065
D	8.32		8.92	0.327		0.351
E	19.00		20.00	0.748		0.787
G	10.70		11.10	0.421		0.437
N	16.50		17.20	0.649		0.677
P	25.00		26.00	0.984		1.023
R	4.00		4.09	0.157		0.161
U	38.50		39.30	1.515		1.547
V	30.00		30.30	1.187		1.193



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